## NSN 5961-01-271-1763

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View Online at https://aerobasegroup.com/nsn/5961-01-271-1763 **Inclosure Material:** Plastic all transistor **Overall Length:** 0.185 inches all transistor **Terminal Length:** 0.500 inches all transistor **Internal Configuration:** Field effect all transistor **Channel Polarity And Control Type (non-core):** N-channel junction type all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 4 transistor **Mounting Method:** Terminal all transistor **Field Force Effect Type:** Electrostatic charge **Features Provided:** Hermetically sealed case and electrostatic sensitive **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 25.0 drain to gate voltage all transistor and 25.0 drain to source voltage all transistor and 25.0 reverse gate to source voltage all transistor **Current Rating Per Characteristic:** 10.00 milliamperes zero-gate-voltage source current horsepower metric all transistor **Power Rating Per Characteristic:** 625.0 milliwatts small-signal input power, common-collector absolute all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction all transistor **Terminal Type And Quantity:** 12 uninsulated wire lead all transistor Shelf Life: N/a **Unit Of Measure: Demilitarization:** No